

ABSTRACT OF THE DISCLOSURE:

A semiconductor photodetecting device including a PIN photodiode formed on an SI-InP substrate; a buried optical waveguide portion formed on the SI-InP substrate and including the film thickness continuously increased toward the PIN photodiode and an InP clad layer covering the upper surface and the side surface of the InGaAsP core layer; and a ridge-shaped connection optical waveguide portion formed on the SI-InP substrate between the PIN photodiode and the buried optical waveguide portion and including the InGaAsP core layer and the InP clad layer selectively covering only the upper surface of the InGaAsP core layer.